EUV photodiode Model SCT-EUV20

General Features:

- SiC-based extreme ultraviolet (EUV) photodiode
- Excellent stability under high fluence EUV exposure
- Photovoltaic mode operation
- Visible blind and low dark current
- High detection efficiency for 13.5 nm EUV radiation
- Ceramic package

Applications: EUV radiation monitoring and flux measurement

Specifications:

Parameters	Symbol	Value	Unit
Maximum ratings			
Operation temperature range	T_{opt}	-20-80	^oC
Storage temperature range	T_{sto}	-55-90	^oC
Soldering temperature (3 s)	T_{sol}	260	^oC
Maxium reverse voltage	$V_{r\text{-}max}$	-20	V
Electro-Optical characteristics (25 ^oC)			
Chip size	A	19.6	mm^2
Spectral response range		5-125	nm
Responsivity (@ 13.5 nm)	R	58	mA/W
Dark current (V_r = -1V)	I_d	< 100	pA
Shunt resistance (@±10mV)	R_{sh}	>10	G
Capacitance (@ 0 V and 1 MHz)	C_p	565	pF
Rise Time (V_r=0 V, R_L			